

# Jiarui Gong

## List of Publications by Year in descending order

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Version: 2024-02-01

10  
papers

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citations

1162367

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1473754

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docs citations

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times ranked

242  
citing authors

#	ARTICLE	IF	CITATIONS
1	Influences of ALD Al <sub>2</sub> O <sub>3</sub> on the surface band-bending of c-plane, Ga-face GaN. Japanese Journal of Applied Physics, 2022, 61, 011003.	0.8	7
2	AlGaIn/GaN Schottky-Gate HEMTs With UV/O <sub>3</sub> -Treated Gate Interface. IEEE Electron Device Letters, 2020, 41, 1488-1491.	2.2	13
3	Metal-Al <sub>2</sub> O <sub>3</sub> -GaN capacitors with an ultraviolet/ozone plasma-treated interface. Japanese Journal of Applied Physics, 2020, 59, 030908.	0.8	8
4	Fabrication of AlGaAs/GaAs/diamond heterojunctions for diamond-collector HBTs. AIP Advances, 2020, 10, .	0.6	11
5	Influences of screw dislocations on electroluminescence of AlGaIn/AlN-based UVC LEDs. AIP Advances, 2019, 9, .	0.6	11
6	Reduction of Leakage Current in GaN Schottky Diodes Through Ultraviolet/Ozone Plasma Treatment. IEEE Electron Device Letters, 2019, 40, 1796-1799.	2.2	18
7	P-type silicon as hole supplier for nitride-based UVC LEDs. New Journal of Physics, 2019, 21, 023011.	1.2	16
8	Toward Diamond-Collector Heterojunction Bipolar Transistors via grafted GaAs-Diamond n-p junction. , 2019, , .		2
9	229-nm UV LEDs on aluminum nitride single crystal substrates using p-type silicon for increased hole injection. Applied Physics Letters, 2018, 112, .	1.5	52
10	226-nm AlGaIn/AlN UV LEDs using p-type Si for hole injection and UV reflection. Applied Physics Letters, 2018, 113, .	1.5	59